

N-channel SiC power MOSFET

V_{DSS}	1700V
R _{DS(on)} (Typ.)	1.15Ω
I _D	4A
P_D	44W

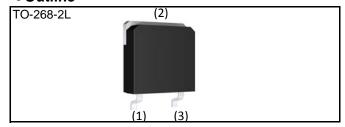
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance with no center lead
- 4) Simple to drive
- 5) Pb-free lead plating; RoHS compliant

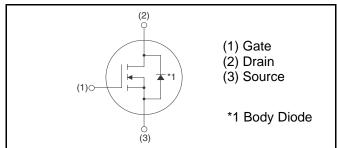
Application

- Auxilialy power supplies
- Switch mode power supplies

Outline



•Inner circuit



Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Type	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	400
	Taping code	ТВ
	Marking	SCT2H12NY

● Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V _{DSS}	1700	V
Continuous drain surrent	T _c = 25°C	I _D *1	4	А
Continuous drain current	T _c = 100°C	I _D *1	2.9	А
Pulsed drain current		I _{D,pulse} *2	10	А
Gate - Source voltage (DC)		V _{GSS}	-6 to 22	V
Gate - Source surge voltage (t _{surge} <300nsec)		V _{GSS_surge} *3	–10 to 26	V
Power dissipation (T _c = 25°C)		P _D	44	W
Junction temperature		Tj	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

●Thermal resistance

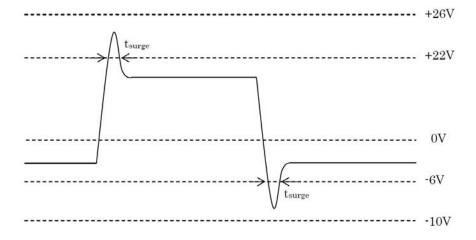
Parameter	Symbol	Values			Unit
r arameter	Symbol	Min.	Тур.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	2.65	3.45	°C/W

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	1700	-	-	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 1700V, V_{GS} = 0V$ $T_{j} = 25^{\circ}C$ $T_{i} = 150^{\circ}C$	-	0.1 0.2	10	μΑ
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS} -	$V_{GS} = -6V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}, I_{D} = 0.41 \text{mA}$	1.6	2.8	4.0	V

^{*1} Limited only by maximum temperature allowed.

*3 Example of acceptable Vgs waveform



*4 Pulsed

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

●Electrical characteristics (T_a = 25°C)

Parameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 18V, I_D = 1.1A$				
Static drain - source on - state resistance	R _{DS(on)} *4	T _j = 25°C	-	1.15	1.5	Ω
		T _j = 125°C	-	1.71	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	64	-	Ω
Transconductance	g fs *4	$V_{DS} = 10V, I_D = 1.1A$	-	0.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	184	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	16	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	6	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 800V	-	17	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 500V, I_D = 1.1A$	-	16	-	
Rise time	t _r *4	V _{GS} = 18V/0V	-	21	-	
Turn - off delay time	t _{d(off)} *4	$R_L = 455\Omega$	-	35	-	ns
Fall time	t _f *4	$R_G = 0\Omega$	-	74	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 800V, I_{D} = 1.1A$ $V_{GS} = 18V/0V$	-	57	-	1
Turn - off switching loss	E _{off} *4	$R_G = 0\Omega$, L=2mH * E_{on} includes diode reverse recovery	-	32	-	μJ

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiailletei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*4}	V _{DD} = 500V	-	14	-	
Gate - Source charge	Q _{gs} *4	I _D = 1A	-	4	-	nC
Gate - Drain charge	Q _{gd} *4	V _{GS} = 18V	-	5	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 500V, I_D = 1A$	-	10.5	-	V

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	-	4	А
Inverse diode direct current, pulsed	I _{SM} *2		-	-	10	А
Forward voltage	V _{SD} *4	$V_{GS} = 0V, I_{S} = 1.1A$	-	4.3	-	V
Reverse recovery time	t _{rr} *4		-	21	ı	ns
Reverse recovery charge	Q _{rr} *4	$I_F = 1.1A, V_R = 800V$ di/dt = 300A/µs	-	13	-	nC
Peak reverse recovery current	I _{rrm} *4		-	1.1	-	Α

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	493m	
R _{th2}	1601m	K/W
R _{th3}	556m	

Symbol	Value	Unit
C _{th1}	378µ	
C _{th2}	1.42m	Ws/K
C _{th3}	65.6m	

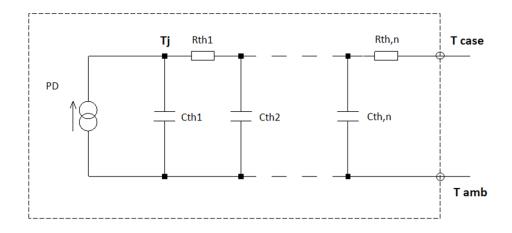


Fig.1 Power Dissipation Derating Curve

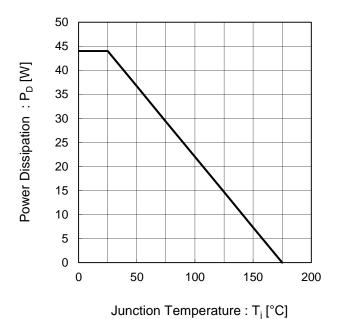
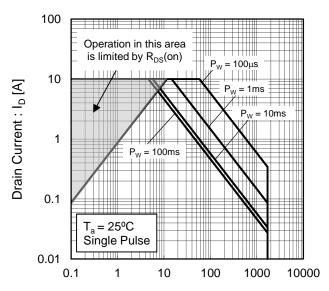
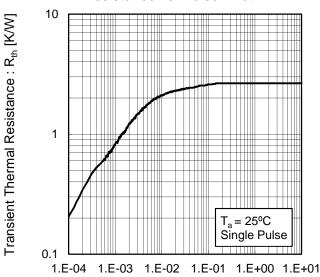


Fig.2 Maximum Safe Operating Area



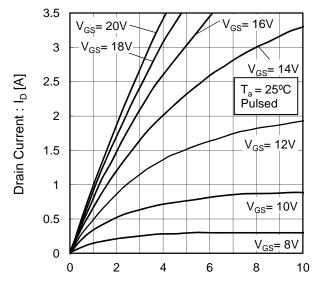
Drain - Source Voltage : V_{DS} [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



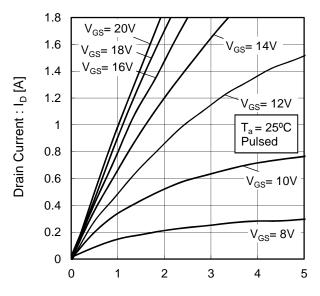
Pulse Width: Pw [s]

Fig.4 Typical Output Characteristics(I)

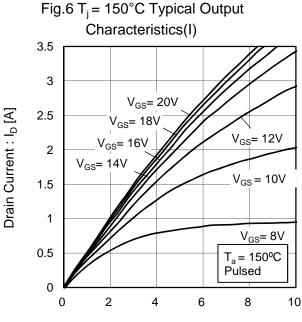


Drain - Source Voltage : V_{DS} [V]

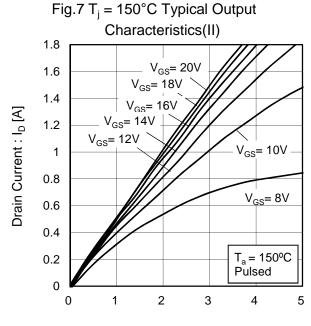
Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

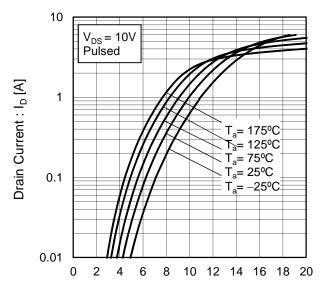


Drain - Source Voltage : V_{DS} [V]



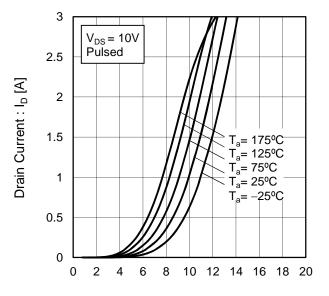
Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Transfer Characteristics (I)



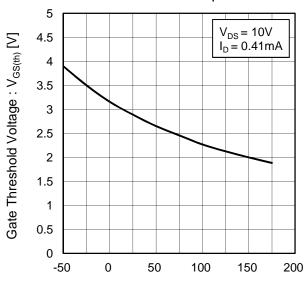
Gate - Source Voltage : V_{GS} [V]

Fig.9 Typical Transfer Characteristics (II)



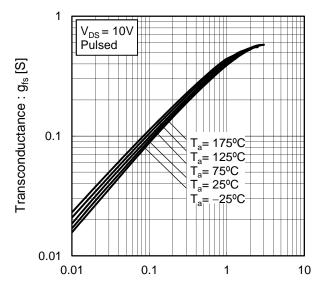
Gate - Source Voltage : V_{GS} [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



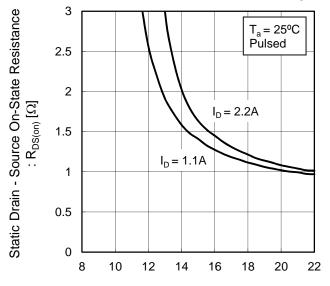
Junction Temperature : T_j [°C]

Fig.11 Transconductance vs. Drain Current



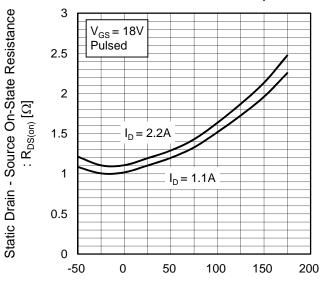
Drain Current : I_D [A]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



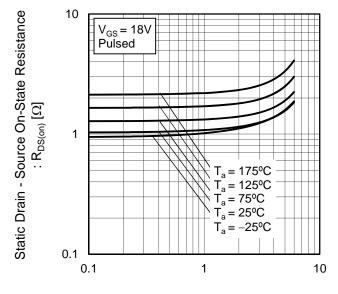
Gate - Source Voltage : V_{GS} [V]

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



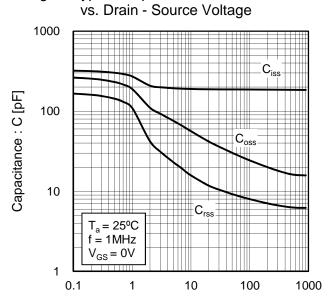
Junction Temperature : T_i [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



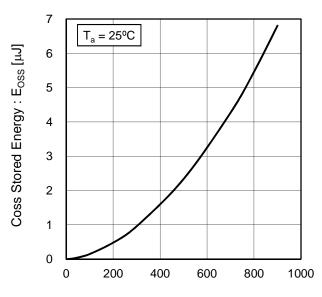
Drain Current : I_D [A]

Fig.15 Typical Capacitance



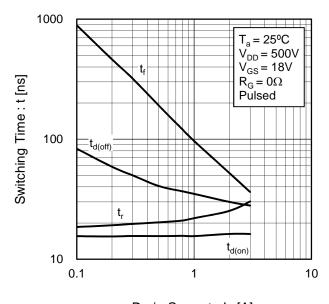
Drain - Source Voltage : V_{DS} [V]

Fig.16 Coss Stored Energy



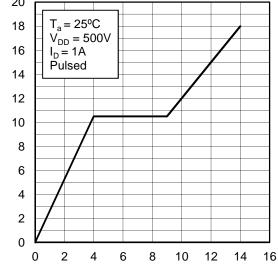
Drain - Source Voltage : V_{DS} [V]

Fig.17 Switching Characteristics



Drain Current : I_D [A]

Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q_g [nC]

Gate - Source Voltage : V_{GS} [V]

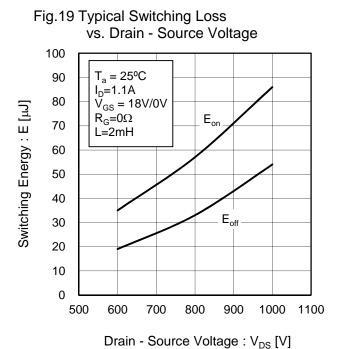


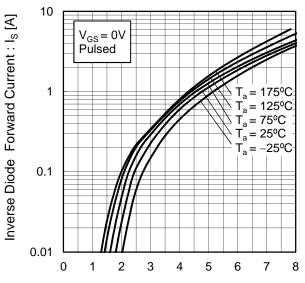
Fig.20 Typical Switching Loss vs. Drain Current 250 $T_a = 25^{\circ}C$ V_{DD}=800V $V_{GS} = 18V/0V$ $R_{G} = 0\Omega$ L = 2mH200 Switching Energy : E [µJ] 150 100 $\mathsf{E}_{\mathsf{off}}$ 50 0 2 3 4 5 0 Drain Current : I_D [A]

Fig.21 Typical Switching Loss vs. External Gate Resistance 140 $T_a = 25^{\circ}C$ V_{DD}=800V 120 E_{on} $I_D = 1.1A$ Switching Energy : E [µJ] $V_{GS} = 18V/0V$ L=2mH 100 80 60 $\mathsf{E}_{\mathsf{off}}$ 40 20 0 20 40 60 80 100 0 External Gate Resistance : $R_G [\Omega]$

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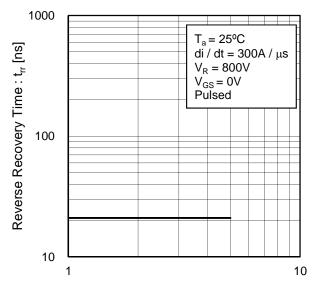
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Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

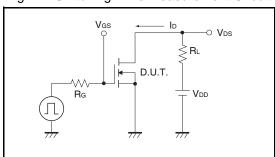


Fig.2-1 Gate Charge Measurement Circuit

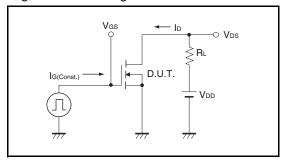


Fig.3-1 Switching Energy Measurement Circuit

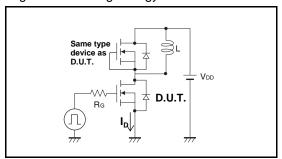


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

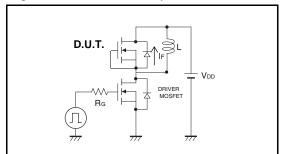


Fig.1-2 Switching Waveforms

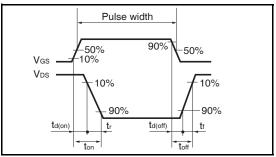


Fig.2-2 Gate Charge Waveform

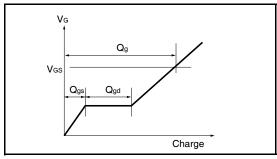
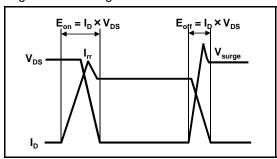
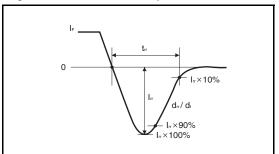


Fig.3-2 Switching Waveforms





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